

NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Parameter	Tr1 and Tr2
$V_{CEO}$	50V
I <sub>C</sub>	100mA
$R_1$	10kΩ

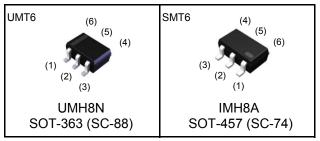
#### Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC114T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

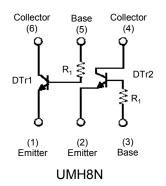
#### Application

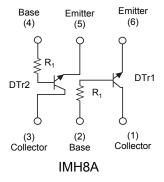
Inverter circuit, Interface circuit, Driver circuit

#### Outline



#### •Inner circuit





#### Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
UMH8N	UMT6	2021	TN	180	8	3,000	H8
IMH8A	SMT6	2928	T110	180	8	3,000	H8

## ● Absolute maximum ratings (Ta = 25°C)

### <For DTr1 and DTr2 in common>

Parameter		Symbol	Values	Unit
Collector-base voltage		$V_{CBO}$	50	V
Collector-emitter voltage		V <sub>CEO</sub> 50		V
Emitter-base voltage		$V_{EBO}$	5	V
Collector current		I <sub>C</sub> *1	100	mA
Collector Power dissipation UMH8N IMH8A		P <sub>D</sub> *2	150 (Total) <sup>*3</sup>	mW
		ΓD	300 (Total)*4	mW
Junction temperature		T <sub>j</sub>	150	°C
Range of storage temperature		T <sub>stg</sub>	−55 to +150	°C

## ●Electrical characteristics(Ta = 25°C)

### <For DTr1 and DTr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	50	-	-	V
Emitter-base breakdown voltage	$BV_{EBO}$	I <sub>E</sub> = 50μA	5	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 50V	-	-	0.5	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	-	-	0.5	μА
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> / I <sub>B</sub> = 10mA / 1mA	-	-	0.3	V
DC current gain	h <sub>FE</sub>	$V_{CE}$ = 5V , $I_{C}$ = 1mA	100	250	600	-
Input resistance	R <sub>1</sub>	-	7	10	13	kΩ
Transition frequency	f <sub>T</sub> *1	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA f = 100MHz	-	250	-	MHz

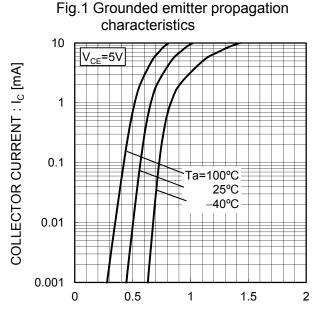
<sup>\*1</sup> Characteristics of built-in transistor

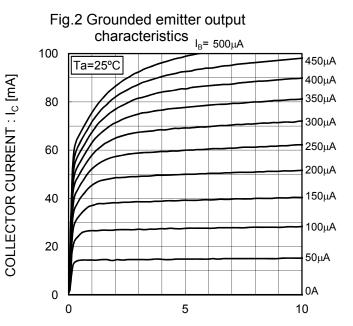
<sup>\*2</sup> Each terminal mounted on a reference footprint

<sup>\*3 120</sup>mW per element must not be exceeded.

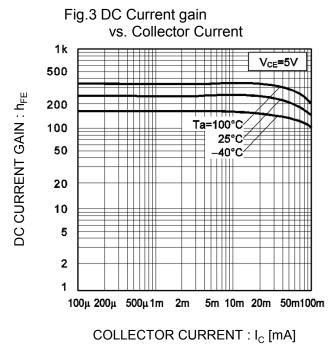
<sup>\*4 200</sup>mW per element must not be exceeded.

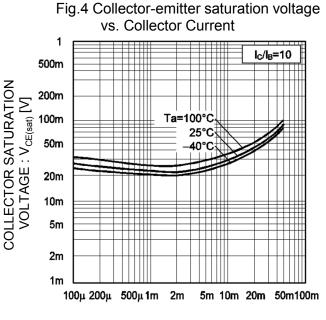
## ●Electrical characteristic curves (Ta = 25°C) <For DTr1 and DTr2 in common>





BASE TO EMITTER VOLTAGE :  $V_{\text{BE}}[V]$  COLLECTOR TO EMITTER VOLTAGE :  $V_{\text{CE}}[V]$ 

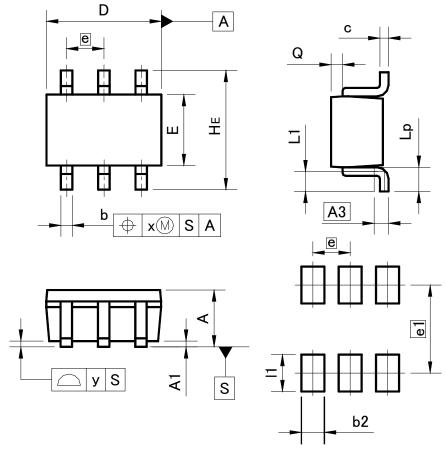




COLLECTOR CURRENT : I<sub>C</sub> [mA]

## ●Dimensions (Unit : mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

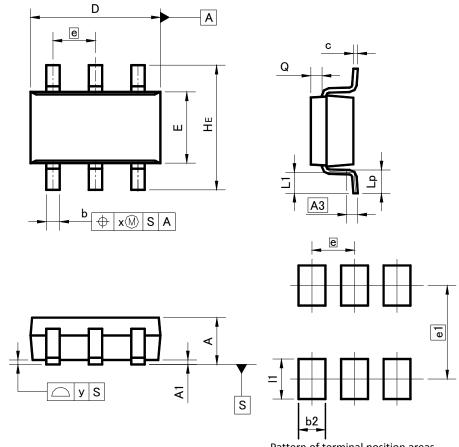
DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.:	25	0.0	10
b	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.	65	0.0	26
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
Х	_	0.10		0.004
У	_	0.10	_	0.004

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	_	0.40	-	0.016	
e1	1.5	1.55		061	
I1	_	0.65	_	0.026	

Dimension in mm / inches

## ●Dimensions (Unit : mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.5	25	0.0	10
b	0.25	0.40	0.010	0.016
С	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
Е	1.50	1.80	0.059	0.071
е	0.9	0.95		37
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х	_	0.20		0.008
У	_	0.10	_	0.004

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
b2		0.60	_	0.024
e1	2.	10	0.083	
l1	_	0.90	_	0.035

Dimension in mm / inches

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